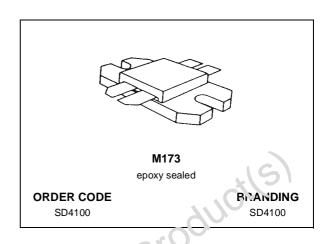


SD4100

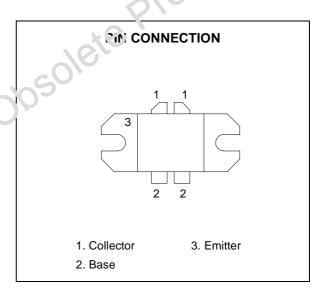
RF POWER TRANSISTORS UHF TV/LINEAR APPLICATIONS

- 470 860 MHz
- 28 VOLTS
- CLASS AB PUSH PULL
- DESIGNED FOR HIGH POWER LINEAR OPERATION
- HIGH SATURATED POWER CAPABILITY
- INTERNAL INPUT/OUTPUT MATCHING NETWORKS PROVIDE HIGH BALANCED IMPEDANCES FOR SIMPLIFIED CIRCUIT DESIGN AND WIDE INSTANTANEOUS BANDWIDTH
- GAIN = 8.5 dB MIN.
- Pout = 100 W MIN. CW
- Pout = 125 W PEAK SYNC



DESCRIPTION

The SD4100 is a gold metallized epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for high linearity Class AE operation in UHF and Band IV, V television transmitters and transposers.



ABSOLUTE MAXIMUM RATINGS (TCASE = 25 °C)

Simbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65	V
V _{CEO}	Collector-Emitter Voltage	32	V
V _{EBO}	Emitter-Base Voltage	3.5	V
Ic	Device Current	16	A
P _{DISS}	Power Dissipation	220	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

_				
	$R_{th(j-c)}$	Junction-Case Thermal Resistance	0.8	°C/W

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ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

STATIC

Symbol		Test Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	I _C = 40 mA	I _E = 0 mA	65			V
BV _{CEO}	I _C = 80 mA	I _B = 0 mA	32			V
BV _{CER}	I _C = 120 mA	R _{BE} = 75 Ω	40			V
BV _{EBO}	I _E = 20 mA	I _C = 0 mA	3.5			V
I _{CEO}	V _{CE} = 28 V	I _B = 0 mA			10	mA
h _{FE}	V _{CE} = 5 V	I _C = 4 A	25		120	

REF.1017623C

DYNAMIC

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
СОВ	$f = 1 \text{ MHz}$ $V_{CB} = 28 \text{ V (each side)}$		50		ςE
OOB	COB is not measurable due to Internal Output Matching Network		30		p⊦

DYNAMIC (CW)

Symbol		Test Conditions					Max.	Unit
P _{1dB}	f = 860 MHz	P _{REF} = 25 W	V _{CC} = 28 V	I _{CQ} = 200 mA	100			W
G _P	f = 860 MHz	P _{OUT} = 100 W	V _{CC} = 28 V	I _{CQ} = 200 mA	8.5			dB
ης	f = 860 MHz	P _{OUT} = 100 W	V _{CC} = 28 V	I _{CQ} = 200 mA	55			%
Load Mismatch	f = 860 MHz ALL PHASE A	P _{OUT} = 100 W NGLES	V _{CC} = 28 V	I _{CQ} = 200 mA	3:1			VSWR

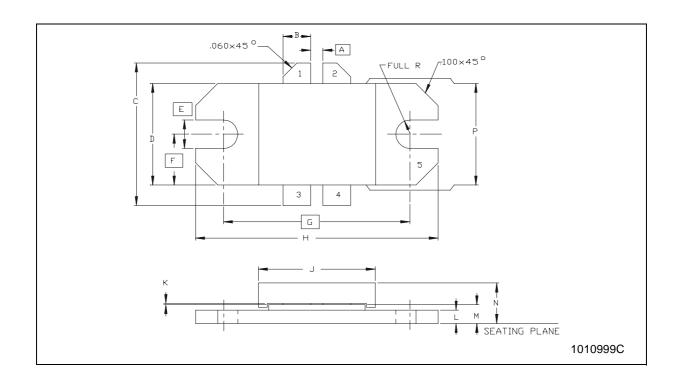
DYNAMIC (VIDEO - STANDARD BLACK LEVEL)

Symbol		Test Conditions					Max.	Unit
G _P	f = 860 MHz	P _{OUT} = 125 W	V _{CC} = 28 V	$I_{CQ} = 200 \text{ mA}$	8.5			dB
P _{1dB}	f = 860 MHz	P _{REF} = 25 W	V _{CC} = 28 V	I _{CQ} = 200 mA	125			W
P _{1dB}	f = 860 MHz	P _{REF} = 25 W	V _{CC} = 32 V	I _{CQ} = 100 mA	150			W

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M173 (.438 X .450 4/L N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			Inch			
DIIVI.	MIN.	TYP.	MAX	MIN.	TYP.	MAX	
Α		1.40			.055		
В	3.05		3.30	.120		.130	
С			19.94			.785	
D	11.56		11.81	.455		.465	
Е		3.30			.130		
F		5.84			.230		
G		21.44			.844		
Н	27.81		28.07	1.095		1.105	
J	13.34		13.59	.525		.535	
K	0.05		0.13	.002		.005	
L	1.40		1.65	.055		.065	
М	2.03		2.41	.080		.095	
N			4.95			.195	
Р	11.30		11.56	.445		.455	



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